CLAIMS

1. A magnetic memory device constructed as a magnetic random access memory, said magnetic memory device comprising:

a memory element having by laminating a magnetization pinned layer in which the orientation of magnetization is pinned and a magnetic layer in which the orientation of magnetization is changeable, and

a magnetic shield layer for magnetically shielding said memory element,

wherein said memory element is characterized by being disposed avoiding an edge portion and a center portion of said magnetic shield layer.

2. A magnetic memory device comprising:

a memory element having a magnetic layer capable of being magnetized, and

a magnetic shield layer for magnetically shielding said memory element,

wherein said memory element is characterized by being disposed avoiding an edge portion and a center portion of said magnetic shield layer.

3. A magnetic memory device according to claim1 or claim2, wherein said memory element is disposed in a region between a position at 0.1 L inward from one side of said maganetic shield layer and a position at 0.15 L outward from the center of said magnetic shield layer toward one side thereof, where a length from one side of said magnetic shield layer to an opposed side thereof is L.

4. A memory device according to claim 3, wherein said memory element is disposed in a region between a position at 0.2 L inward from said one side and a position at 0.15 L outward from the center of said shield layer toward said one side thereof, where said magnetic shield layer is provided on both sides of said memory element, and a distance between said magnetic shield layers, a length from said one side of said magnetic shield layer to the opposed side thereof, and an external magnetic field to be applied are constant respectively.

5. A memory device according to claim 3, wherein said memory element is disposed in a region between a position at 0.1 L inward from said one side thereof and a position at 0.2 L outward from the center of the shield layer toward said one side thereof, where a distance between said magnetic shield layers, a thickness of said magnetic shield layers, and an external magnetic field to be applied are constant respectively.

6. A memory device according to claim 1 or claim2, wherein said magnetic shield layer is disposed on the top and/or bottom of a package having by sealing said memory element therein, or/and on the upper portion and/or the lower portion of said memory element within said package.

7. A memory device according to claim 6, wherein said memory element is present almost allover said package.

8. A memory device according to claim 1 or claim2, wherein said magnetic shield layer is in the form of a flat film or plate, or having concave and/or convex portions thereon, or through-holes such as mesh or slits.

9. A memory device according to claim 6, wherein said magnetic shield layer is formed of soft magnetic material that exhibits saturation magnetism at 1.8 tesla or more.

10. A memory device according to claim 1, wherein said memory device is constructed such that an insulating material layer or a conductive material layer is sandwiched between said magnetization pinned layer and said magnetic layer, that with a magnetic field induced by passing a respective current through wirings provided on the top and the bottom of said memory element, the orientation of magnetization in said magnetic layer is aligned in a prescribed direction thereby writing information thereto, and that said written information is read out by use of the tunnel magnetoresistance effect between said wirings.